

IGBT - Field Stop

600 V, 60 A

FGH60N60SFD

Description

Using novel field stop IGBT technology, ON Semiconductor's field stop IGBTs offer the optimum performance for solar inverter, UPS, welder and PFC applications where low conduction and switching losses are essential.

Features

- High Current Capability
- Low Saturation Voltage: $V_{CE(sat)} = 2.3 \text{ V @ } I_C = 60 \text{ A}$
- High Input Impedance
- Fast Switching
- This Device is Pb-Free and is RoHS Compliant

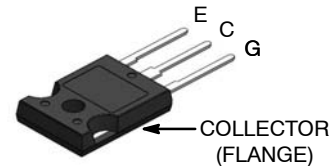
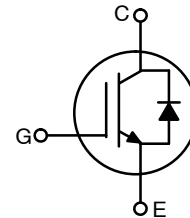
Applications

- Solar Inverter, UPS, Welder, PFC



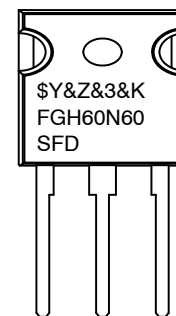
ON Semiconductor®

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TO-247-3LD
CASE 340CK

MARKING DIAGRAM



\$Y	= ON Semiconductor Logo
&Z	= Assembly Plant Code
&3	= Numeric Date Code
&K	= Lot Code
FGH60N60SFD	= Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

FGH60N60SFD

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Description		Symbol	Ratings	Unit
Collector to Emitter Voltage		V _{CES}	600	V
Gate to Emitter Voltage		V _{GES}	±20	V
Transient Gate-to-Emitter Voltage			±30	
Collector Current	T _C = 25°C	I _C	120	A
Collector Current	T _C = 100°C		60	A
Pulsed Collector Current	T _C = 25°C	I _{CM} (Note 1)	180	A
Maximum Power Dissipation	T _C = 25°C	P _D	378	W
Maximum Power Dissipation	T _C = 100°C		151	W
Operating Junction Temperature		T _J	–55 to +150	°C
Storage Temperature Range		T _{stg}	–55 to +150	°C
Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds		T _L	300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive test, Pulse width limited by max. junction temperature.

THERMAL CHARACTERISTICS

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance, Junction to Case	R _{θJC} (IGBT)	–	0.33	°C/W
Thermal Resistance, Junction to Case	R _{θJC} (Diode)	–	1.1	°C/W
Thermal Resistance, Junction to Ambient	R _{θJA}	–	40	°C/W

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FGH60N60SFDTU	FGH60N60SFD	TO-247	Tube	N/A	N/A	30

ELECTRICAL CHARACTERISTICS OF THE IGBT (T_C = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector to Emitter Breakdown Voltage	BV _{CES}	V _{GE} = 0 V, I _C = 250 μA	600	–	–	V
Temperature Coefficient of Breakdown Voltage	ΔBV _{CES} /ΔT _J	V _{GE} = 0 V, I _C = 250 μA	–	0.4	–	V/°C
Collector Cut-Off Current	I _{CES}	V _{CE} = V _{CES} , V _{GE} = 0 V	–	–	250	μA
G–E Leakage Current	I _{GES}	V _{GE} = V _{GES} , V _{CE} = 0 V	–	–	±400	nA

ON CHARACTERISTICS

G–E Threshold Voltage	V _{GE(th)}	I _C = 250 μA, V _{CE} = V _{GE}	4.0	5.0	6.5	V
Collector to Emitter Saturation Voltage	V _{CE(sat)}	I _C = 60 A, V _{GE} = 15 V	–	2.3	2.9	V
		I _C = 60 A, V _{GE} = 15 V, T _C = 125°C	–	2.5	–	V

FGH60N60SFD

ELECTRICAL CHARACTERISTICS OF THE IGBT ($T_C = 25^\circ\text{C}$ unless otherwise noted) (continued)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ies}	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	–	2820	–	pF
Output Capacitance	C_{oes}		–	350	–	pF
Reverse Transfer Capacitance	C_{res}		–	140	–	pF

SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(on)}$	$V_{CC} = 400\text{ V}, I_C = 60\text{ A},$ $R_G = 5\ \Omega, V_{GE} = 15\text{ V},$ Inductive Load, $T_C = 25^\circ\text{C}$	–	22	–	ns
Rise Time	t_r		–	42	–	ns
Turn-Off Delay Time	$t_{d(off)}$		–	134	–	ns
Fall Time	t_f		–	31	62	ns
Turn-On Switching Loss	E_{on}		–	1.79	–	mJ
Turn-Off Switching Loss	E_{off}		–	0.67	–	mJ
Total Switching Loss	E_{ts}			2.46	–	mJ
Turn-On Delay Time	$t_{d(on)}$	$V_{CC} = 400\text{ V}, I_C = 60\text{ A},$ $R_G = 5\ \Omega, V_{GE} = 15\text{ V},$ Inductive Load, $T_C = 125^\circ\text{C}$	–	22	–	ns
Rise Time	t_r		–	44	–	ns
Turn-Off Delay Time	$t_{d(off)}$		–	144	–	ns
Fall Time	t_f		–	43	–	ns
Turn-On Switching Loss	E_{on}		–	1.88	–	mJ
Turn-Off Switching Loss	E_{off}		–	1.0	–	mJ
Total Switching Loss	E_{ts}		–	2.88	–	mJ
Total Gate Charge	Q_g	$V_{CE} = 400\text{ V}, I_C = 60\text{ A}, V_{GE} = 15\text{ V}$	–	198	–	nC
Gate to Emitter Charge	Q_{ge}		–	22	–	nC
Gate to Collector Charge	Q_{gc}		–	106	–	nC

ELECTRICAL CHARACTERISTICS OF THE DIODE ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions		Min	Typ	Max	Unit
V _{FM}	Diode Forward Voltage	I _F = 30 A	T _C = 25°C	–	2.0	2.6	V
			T _C = 125°C	–	1.8	–	
t _{rr}	Diode Reverse Recovery Time	I _F = 30 A, di _F /dt = 200 A/μs	T _C = 25°C	–	47	–	ns
			T _C = 125°C	–	179	–	
Q _{rr}	Diode Reverse Recovery Charge		T _C = 25°C	–	83	–	nC
			T _C = 125°C	–	567	–	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL PERFORMANCE CHARACTERISTICS

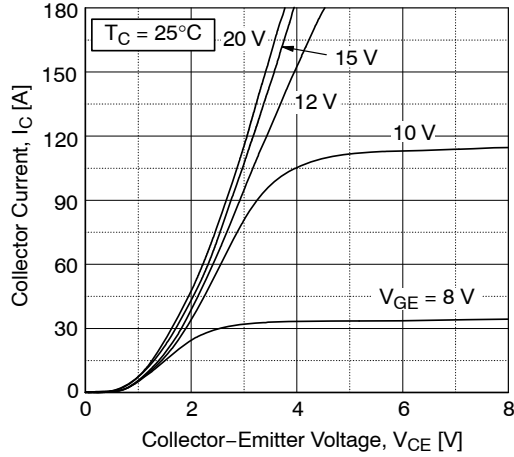


Figure 1. Typical Output Characteristics

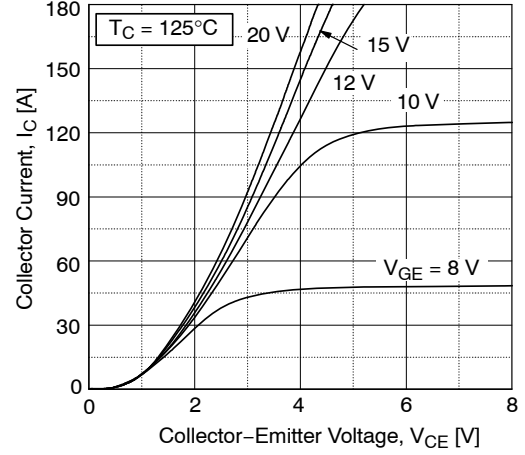


Figure 2. Typical Output Characteristics

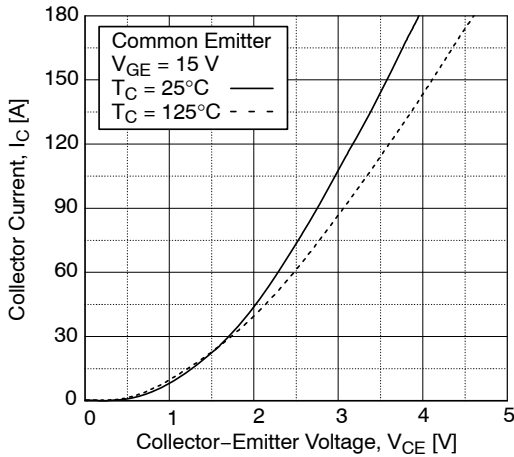


Figure 3. Typical Saturation Voltage Characteristics

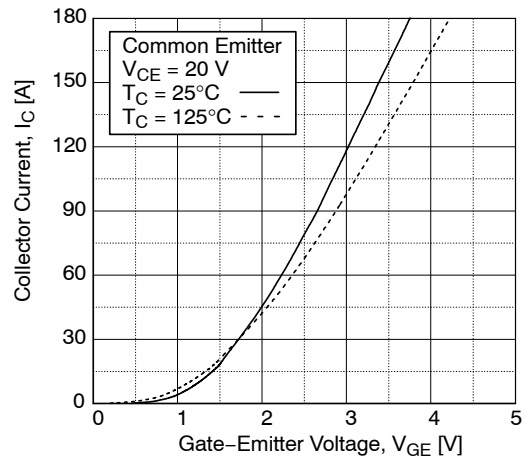


Figure 4. Transfer Characteristics

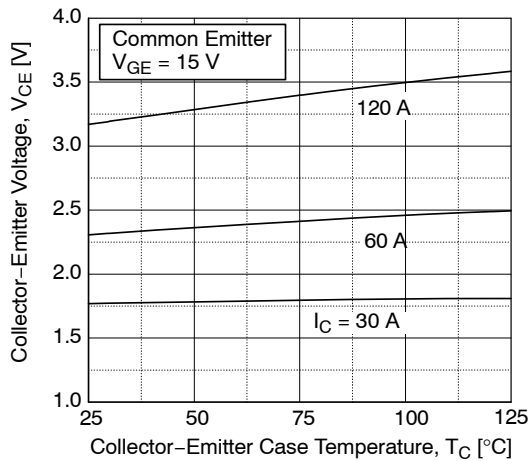


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

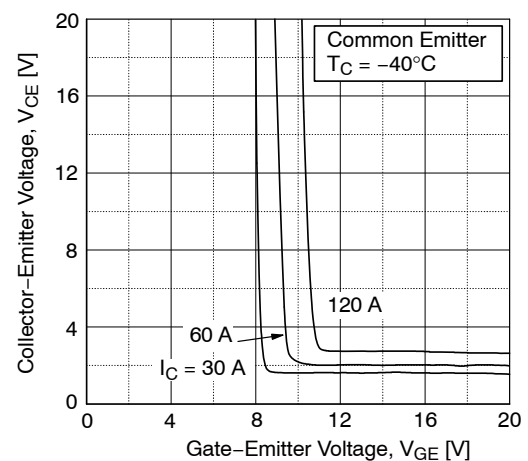


Figure 6. Saturation Voltage vs V_{GE}

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

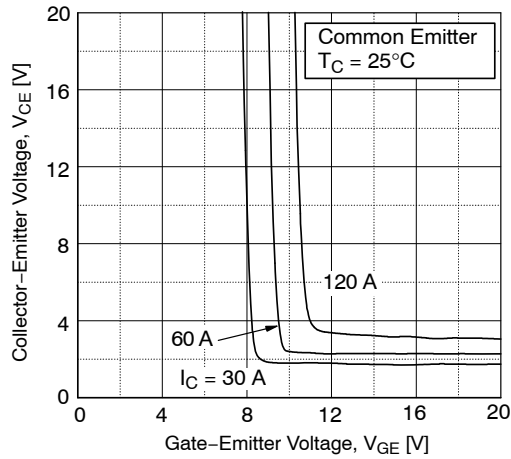


Figure 7. Saturation Voltage vs. V_{GE}

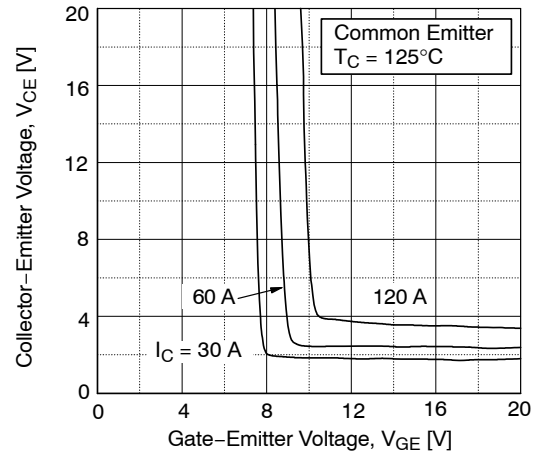


Figure 8. Saturation Voltage vs. V_{GE}

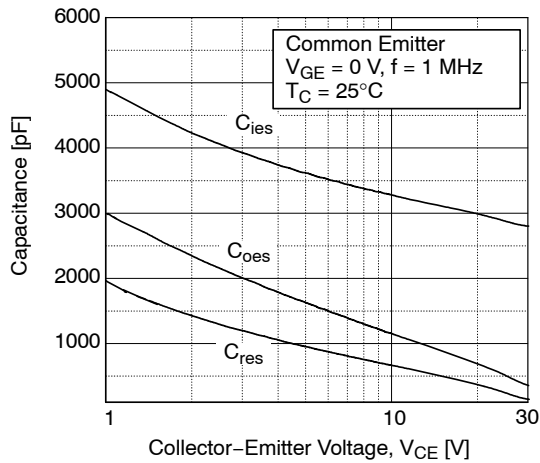


Figure 9. Capacitance Characteristics

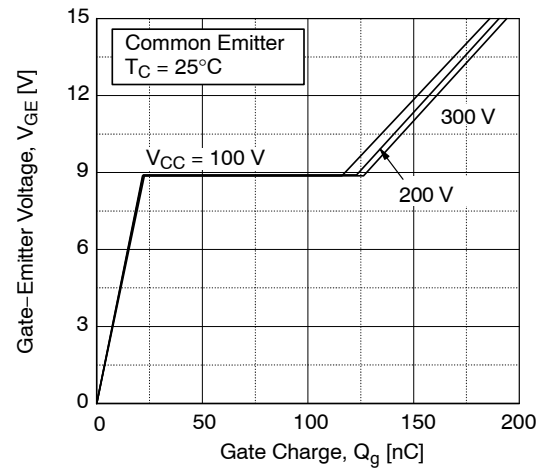


Figure 10. Gate Charge Characteristics

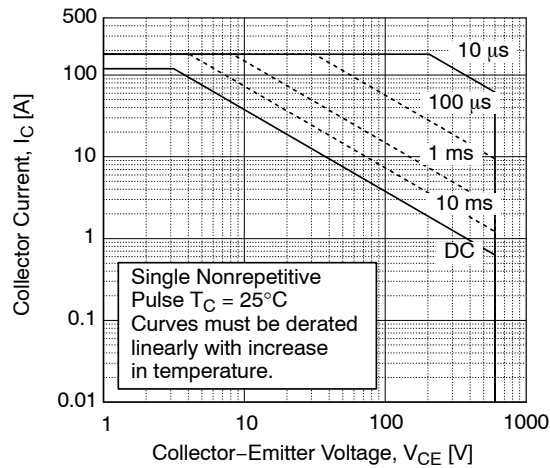


Figure 11. SOA Characteristics

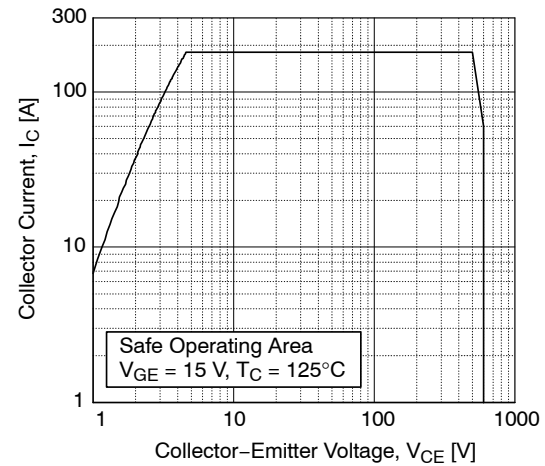


Figure 12. Turn-Off Switching SOA Characteristics

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

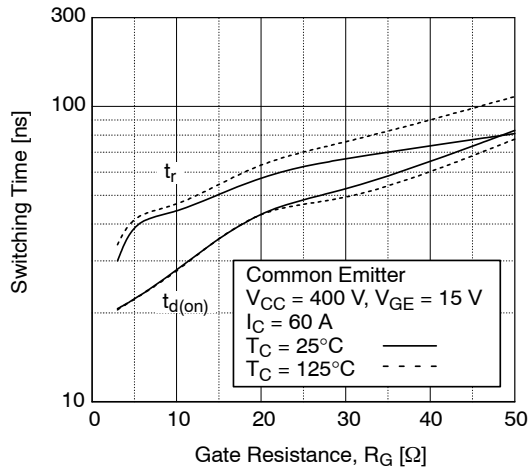


Figure 13. Turn-On Characteristics vs. Gate Resistance

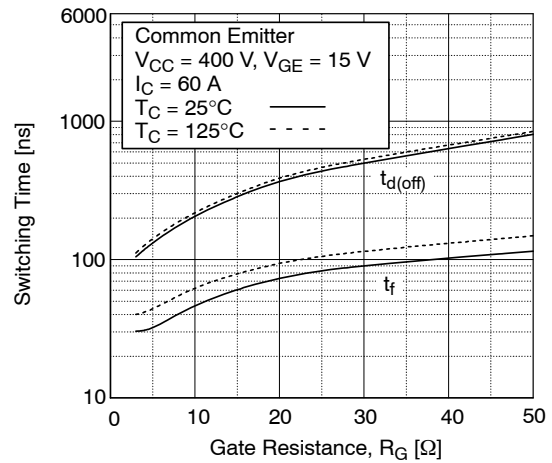


Figure 14. Turn-Off Characteristics vs. Gate Resistance

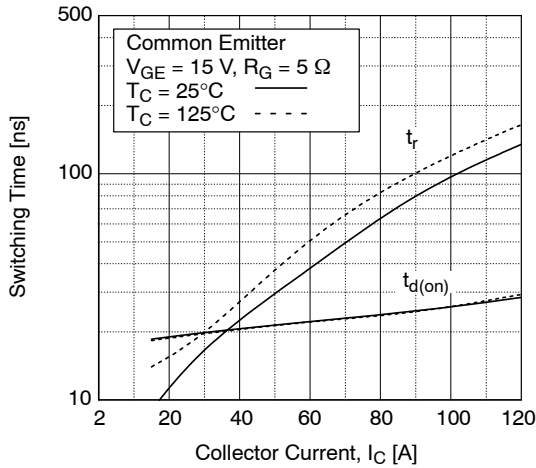


Figure 15. Turn-On Characteristics vs. Collector Current

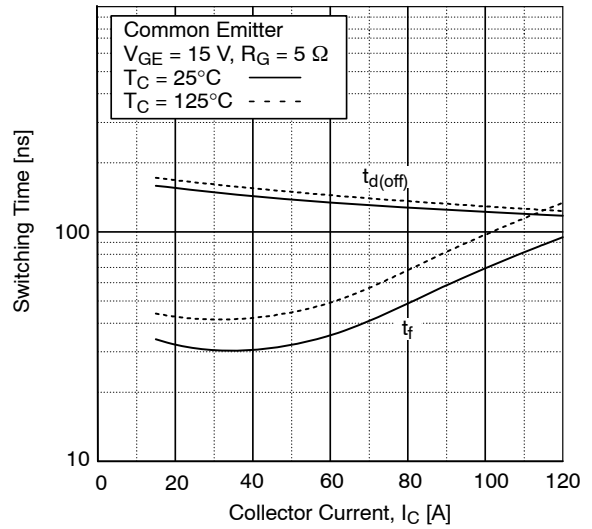


Figure 16. Turn-Off Characteristics vs. Collector Current

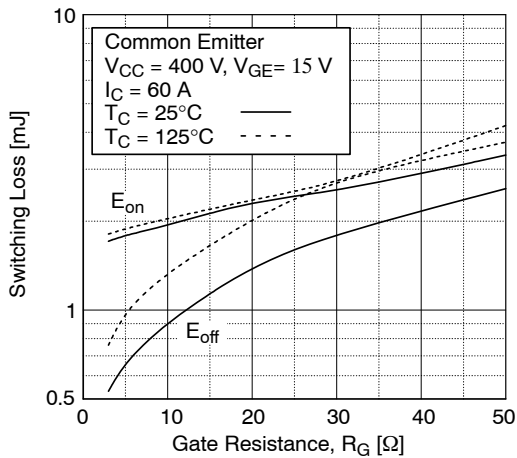


Figure 17. Switching Loss vs. Gate Resistance

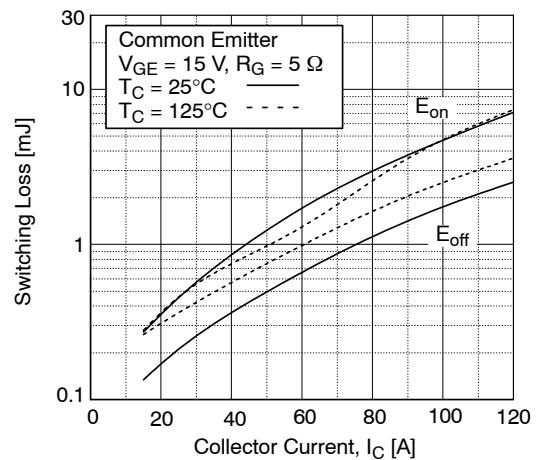


Figure 18. Switching Loss vs. Collector Current

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

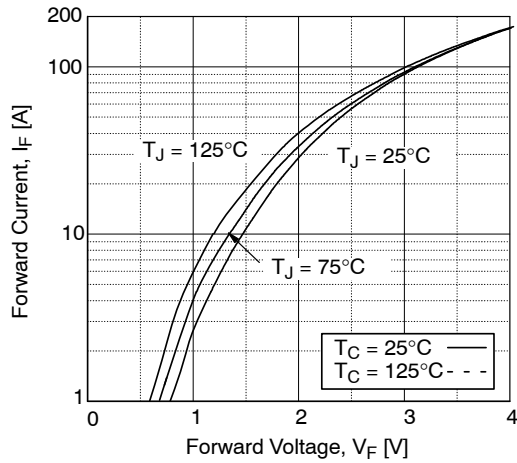


Figure 19. Forward Characteristics

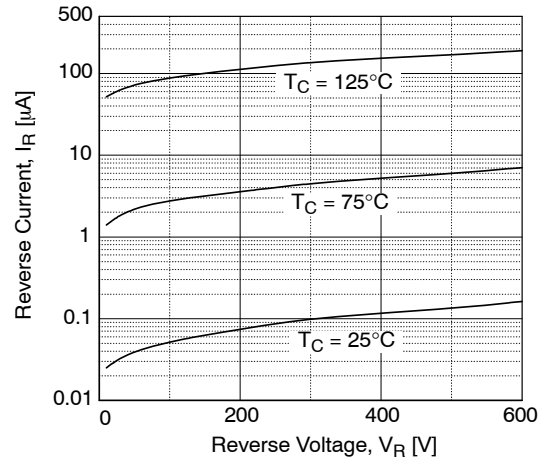


Figure 20. Reverse Current

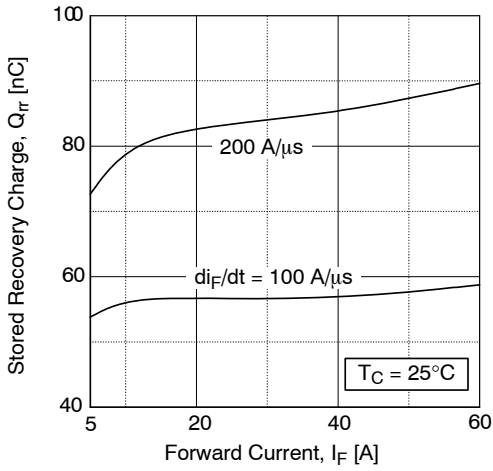


Figure 21. Stored Charge

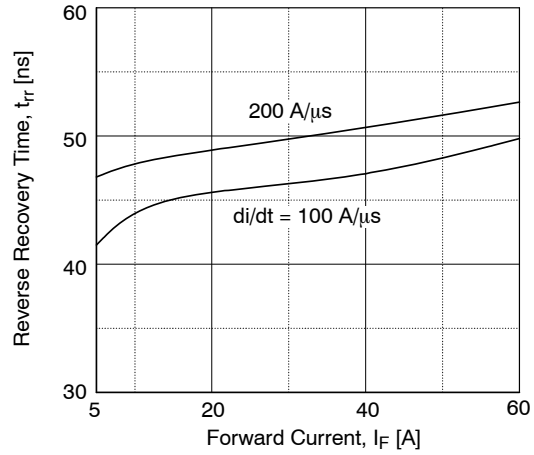


Figure 22. Reverse Recovery Time

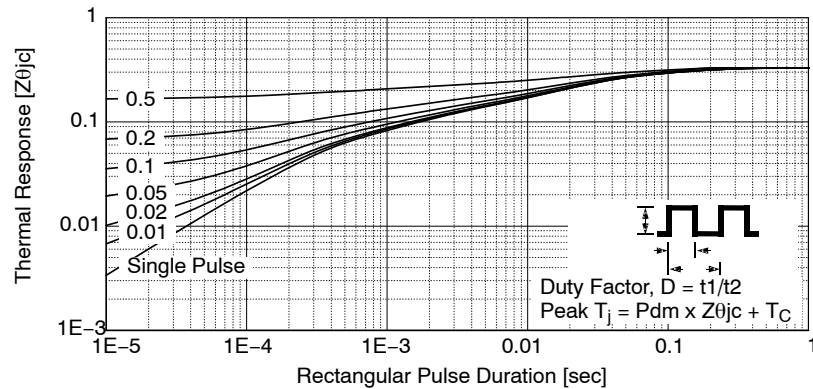
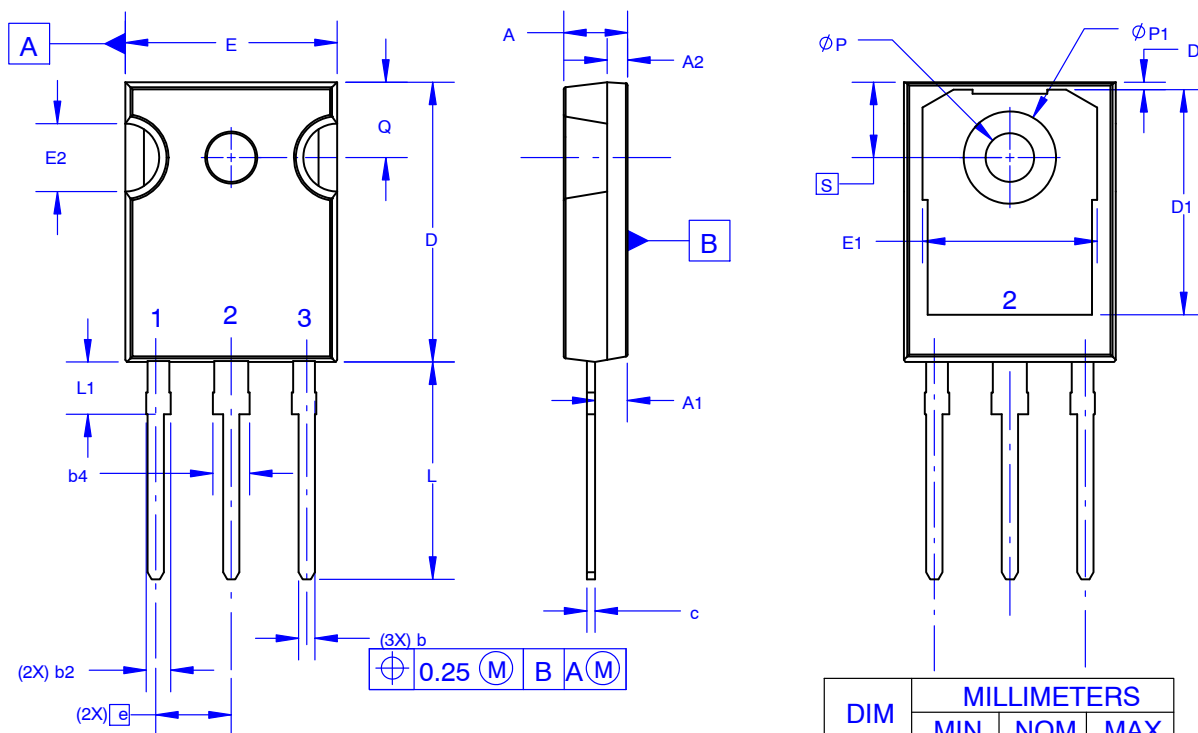


Figure 23. Transient Thermal Impedance of IGBT

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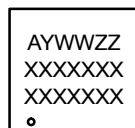
DATE 31 JAN 2019



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D	20.32	20.57	20.82
D1	13.08	~	~
D2	0.51	0.93	1.35
E	15.37	15.62	15.87
E1	12.81	~	~
E2	4.96	5.08	5.20
e	~	5.56	~
L	15.75	16.00	16.25
L1	3.69	3.81	3.93
ϕP	3.51	3.58	3.65
$\phi P1$	6.60	6.80	7.00
Q	5.34	5.46	5.58
S	5.34	5.46	5.58

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DESCRIPTION:	TO-247-3LD SHORT LEAD	PAGE 1 OF 1

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